

<p><b>61056</b></p>	<p><b>PHOTODARLINGTON "PILL PACK" (TYPE GS1030)</b></p>	<p><b>Mii</b> OPTOELECTRONIC PRODUCTS DIVISION</p>
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<p><b>Features:</b></p> <ul style="list-style-type: none"> <li>• Hermetically sealed</li> <li>• High sensitivity</li> <li>• Small package</li> <li>• Suitable for high-density pc board mounting</li> <li>• Spectrally matched to the 62000 series LED.</li> </ul>	<p><b>Applications:</b></p> <ul style="list-style-type: none"> <li>• Incremental encoding</li> <li>• Reflective sensors</li> <li>• Position sensors</li> <li>• Level sensors</li> </ul>
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**DESCRIPTION**

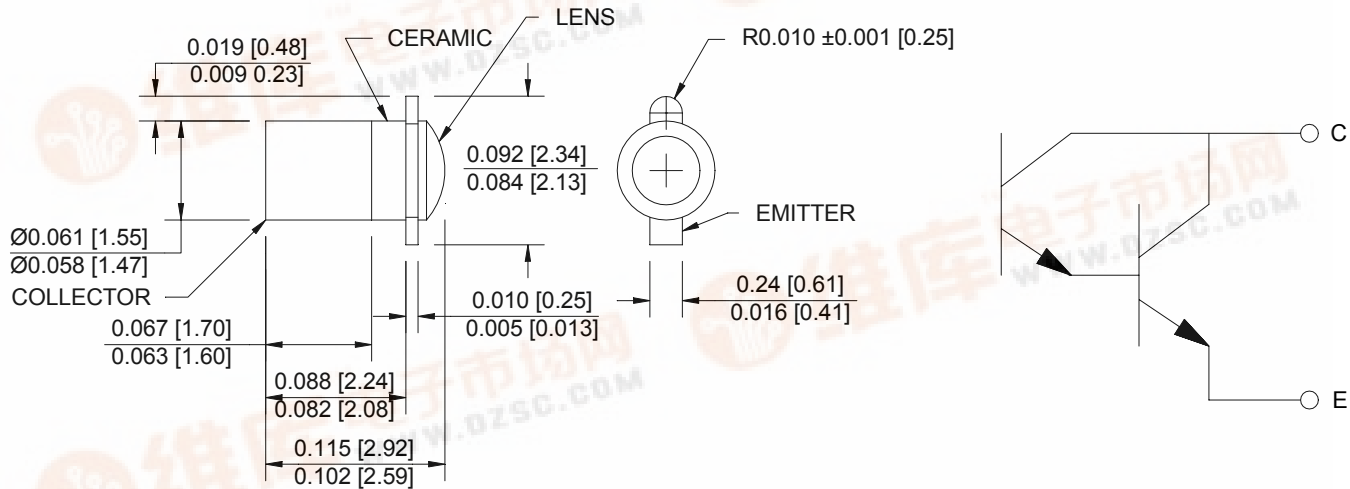
The **61056** is an N-P-N Planar Silicon Photodarlington Transistor in a package designed to be mounted in a double-clad printed circuit board and used in low light level applications. It is available in a range of sensitivities and is lensed for minimum response to stray light. High sensitivity, low dark current leakage, and low saturation voltage make this device ideal for interfacing with TTL circuits. Available custom binned to customer specifications or screened to MIL-PRF-19500.

**ABSOLUTE MAXIMUM RATINGS**

Storage Temperature.....	-65°C to +150°C
Operating Temperature (See part selection guide for actual operating temperature) .....	-65°C to +125°C
Collector-Emitter Voltage.....	50V
Emitter-Collector Voltage.....	7V
Power Dissipation (Derate at the rate of 0.5 mW/°C above 25°C) .....	50mW
Lead Soldering Temperature (3 minutes) .....	240°C

**Package Dimensions**

**Schematic Diagram**



ALL DIMENSIONS ARE IN INCHES [MILLIMETERS]



# 61056

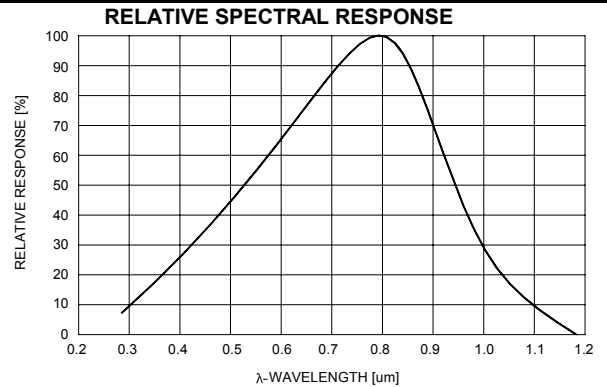
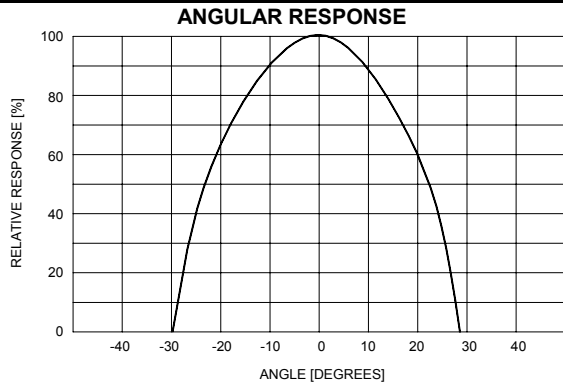
## SILICON PHOTODARLINGTON "PILL PACK" (TYPE GS1030)

### ELECTRICAL CHARACTERISTICS $T_A = 25^\circ\text{C}$ unless otherwise specified.

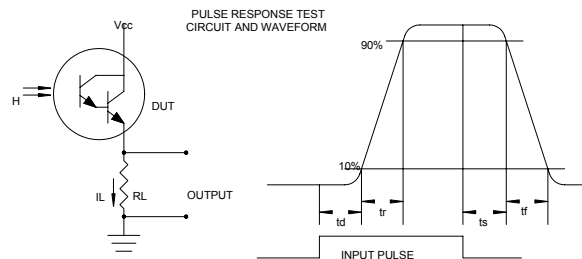
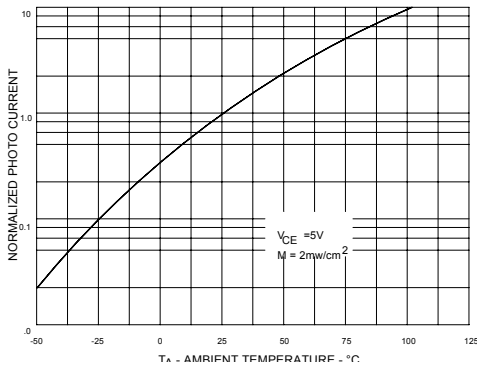
PARAMETER	SYMBOL	MIN	TYP	MAX	UNITS	TEST CONDITIONS	NOTE
Light Current	61056-X01 61056-X02 61056-X03	1 3 6		4 7 --	mA	$V_{CE} = 5.0\text{V}$ , $H = 1.0\text{mW/cm}^2$	1
Dark Current	61056-XXX			250	nA	$V_{CE} = 10\text{V}$ , $H = 0$	1
Collector-Emitter Breakdown Voltage	61056-XXX	15			V	$I_C = 100\mu\text{A}$	
Emitter-Collector Breakdown Voltage	61056-XXX	5			V	$I_E = 100\mu\text{A}$	
Light Current Rise Time	61056-X01 61056-X02 61056-X03		15 25 25		$\mu\text{s}$ $\mu\text{s}$ $\mu\text{s}$	$R_L = 100\Omega$ , $V_{CE} = 5\text{V}$ , $I_L = 1.0\text{mA}$	
Saturation Voltage	61056-X0X		1.1		V	$I_C = 1\text{mA}$ , $H = 1.0\text{mW/cm}^2$	
Angular Response	61056-X0X		24		degrees		2

#### NOTES:6

- Irradiance in  $\text{mW/cm}^2$  from a tungsten source at a color temperature of 2870K.
- The angle between incidence for peak response and incidence for 50% of peak response.



#### PHOTO CURRENT versus TEMPERATURE



#### RECOMMENDED OPERATING CONDITIONS:

PARAMETER	SYMBOL	MIN	MAX	UNITS
Bias Voltage-Collector/Emitter	$I_F$	5	10	mA
Irradiance (H)	H	15	25	$\text{mW/cm}^2$

#### SELECTION GUIDE

PART NUMBER	PART DESCRIPTION	$I_L$ Range
61056-001	Silicon Photodarlington in pill package, commercial version	1 to 4mA
66156-101	Silicon Photodarlington in pill package (-55° to +100°C) with 100% screening	1 to 4mA
61056-002	Silicon Photodarlington in pill package, commercial version	3 to 7mA
61056-102	Silicon Photodarlington in pill package (-55° to +100°C) with 100% screening	3 to 7mA
61056-003	Silicon Photodarlington in pill package, commercial version	6+mA
61056-103	Silicon Photodarlington in pill package (-55° to +100°C) with 100% screening	6+mA